



TO-92 Plastic-Encapsulate Transistors

A94 TRANSISTOR (PNP)

FEATURES

Power dissipation

P_{CM} : 0.625 W ($T_{amb}=25^{\circ}C$)

Collector current

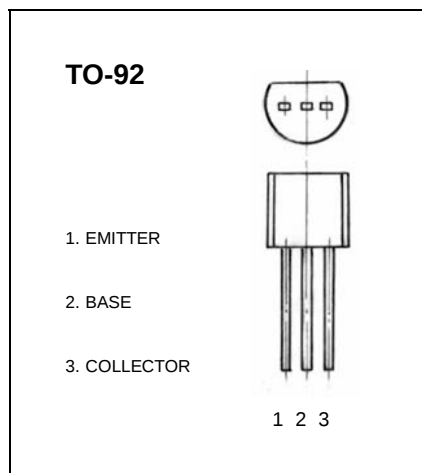
I_{CM} : -0.2 A

Collector-base voltage

$V_{(BR)CBO}$: -400 V

Operating and storage junction temperature range

T_J, T_{stg} : $-55^{\circ}C$ to $+150^{\circ}C$



ELECTRICAL CHARACTERISTICS ($T_{amb}=25^{\circ}C$ unless otherwise specified)

Parameter	Symbol	Test conditions	MIN	TYP	MAX	UNIT
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C = -100\mu A, I_E = 0$	-400			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C = -1 mA, I_B = 0$	-400			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E = -100\mu A, I_C = 0$	-5			V
Collector cut-off current	I_{CBO}	$V_{CB} = -400V, I_E = 0$			-0.1	μA
Collector cut-off current	I_{CEO}	$V_{CE} = -400V, I_B = 0$			-5	μA
Emitter cut-off current	I_{EBO}	$V_{EB} = -4V, I_C = 0$			-0.1	μA
DC current gain	$h_{FE(1)}$	$V_{CE} = -10V, I_C = -10 mA$	80		300	
	$h_{FE(2)}$	$V_{CE} = -10V, I_C = -1mA$	70			
	$h_{FE(3)}$	$V_{CE} = -10V, I_C = -100 mA$	60			
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C = -10 mA, I_B = -1mA$			-0.2	V
	$V_{CE(sat)}$	$I_C = -50 mA, I_B = -5mA$			-0.3	V
Base-emitter saturation voltage	$V_{BE(sat)}$	$I_C = -10 mA, I_B = -1 mA$			-0.75	V
Transition frequency	f_T	$V_{CE} = -20V, I_C = -10mA$ $f = 30MHz$	50			MHz